

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	708	etch\$3 same (SAC or (self adj align\$4 adj contact) or contact or hole or node or nodal) same ((sidewall or spacer) with (nitride of "silicon nitride" or "Si.sub.3N.sub.4" or SiN)) same (CVD or "chemical vapor deposition")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 15:27			
2	BRS	L2	708	etch\$3 same (SAC or (self adj align\$4 adj contact) or contact or hole or node or nodal) same ((sidewall or spacer) with (nitride of "silicon nitride" or "Si.sub.3N.sub.4" or SiN)) same (CVD or "chemical vapor deposition")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 17:12			
3	BRS	L3	452	2 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 17:12			
4	BRS	L4	292	3 and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 15:29			
5	BRS	L5	0	(bufer with ("silicon oxide" or "silicon dioxide")) same (thermal with oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 17:11			
6	BRS	L6	191	(buffer with ("silicon oxide" or "silicon dioxide")) same (thermal with oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 17:11			
7	BRS	L7	106	6 and @pd<="20031114"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 17:12			
8	BRS	L8	9	6 same (SAC or (self adj align\$4 adj contact) or contact or hole or node or nodal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/08 17:14			